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ESD



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MOV



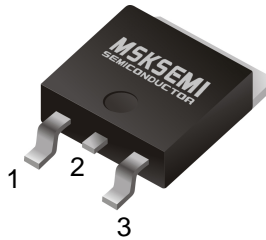
GDT



PLED

Product data sheet

www.msksemi.com



TO-252-2L

TRANSISTOR (NPN)

FEATURES

Power Dissipation

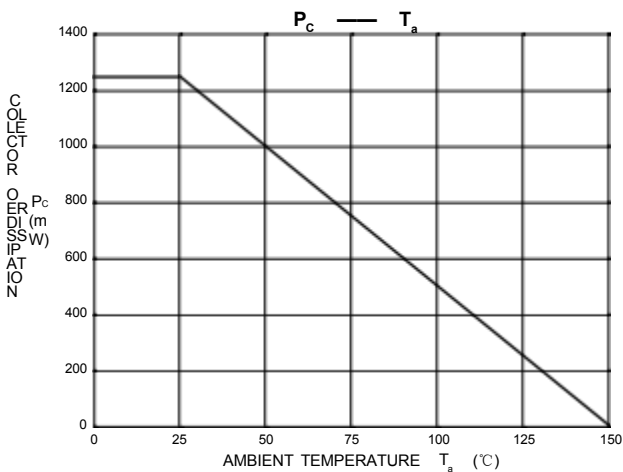
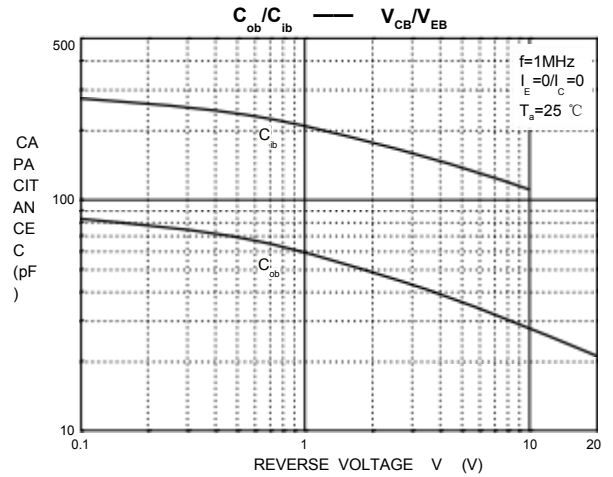
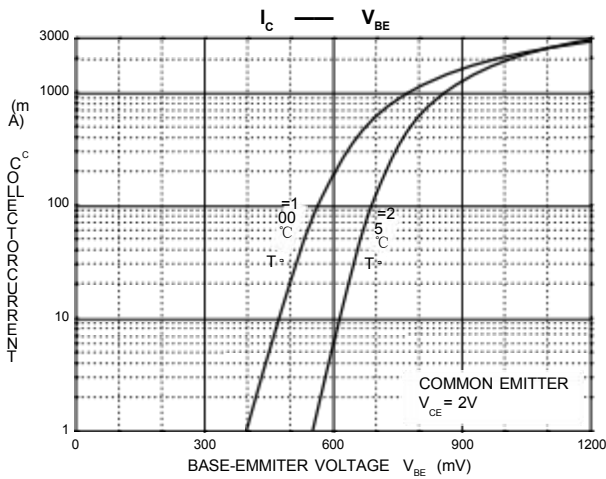
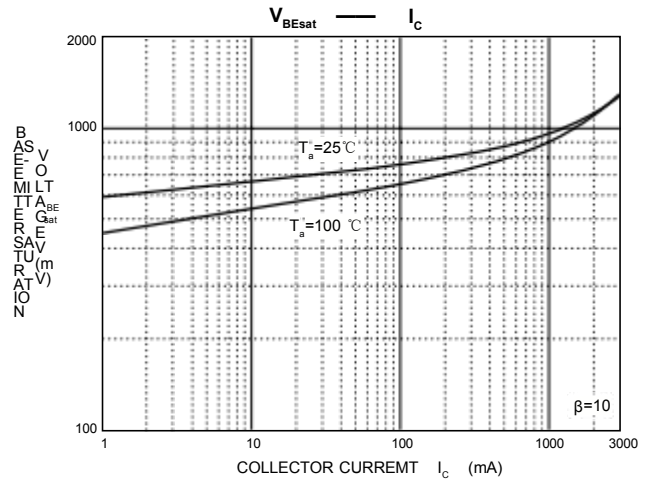
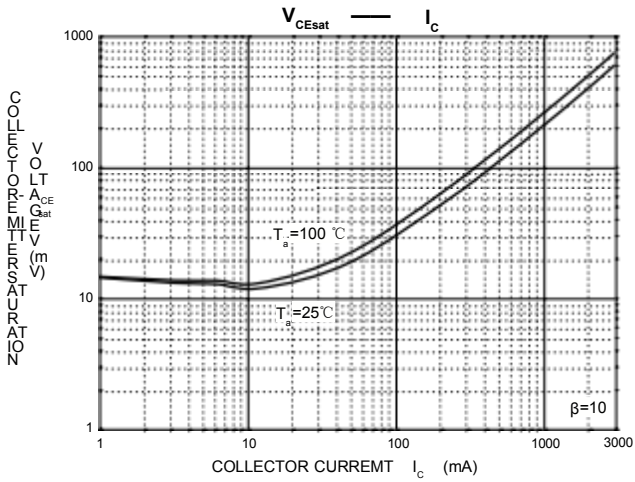
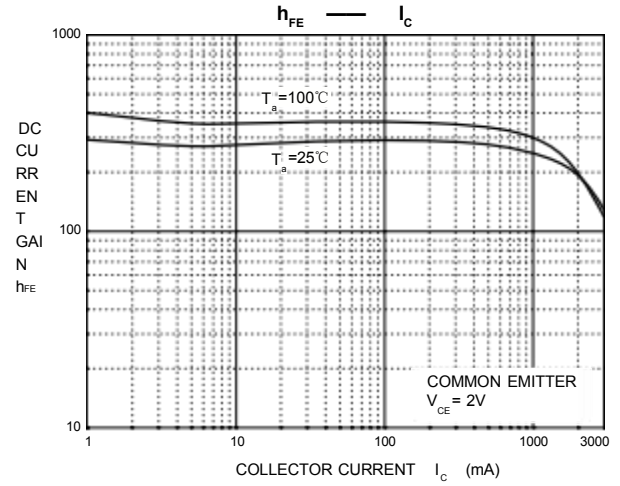
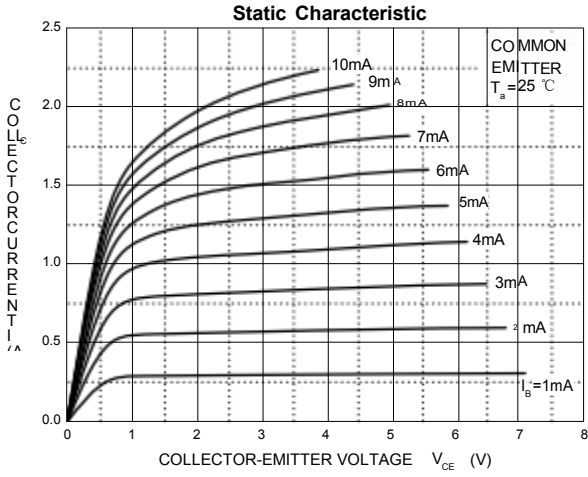
- 1. BASE
- 2. COLLECTOR
- 3 .EMITTER

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

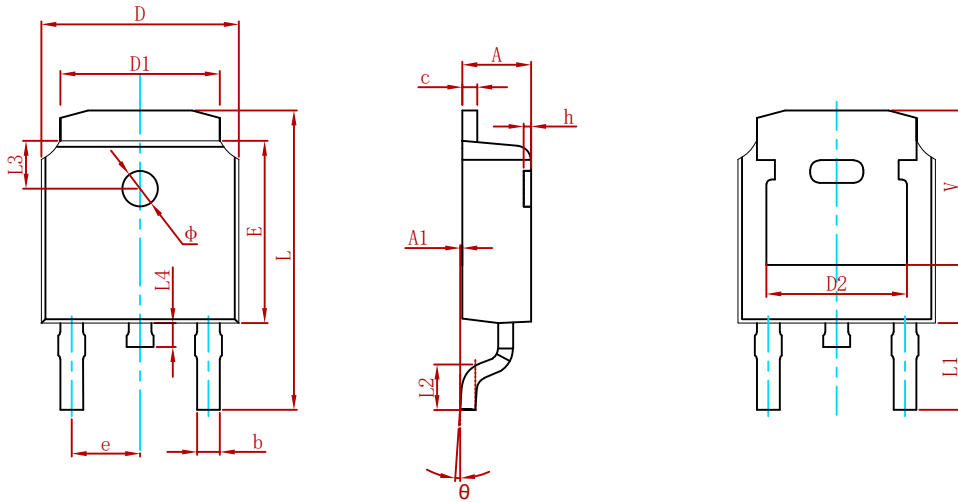
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	6	V
I _c	Collector Current -Continuous	3	A
P _c	Collector Power Dissipation	1.25	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

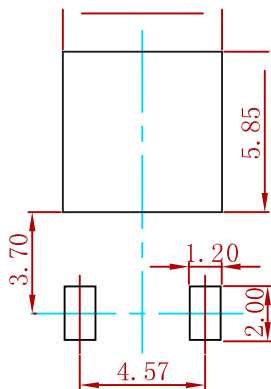
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _c = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _c = 10mA, I _B =0	40			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100μA, I _c =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} = 40 V, I _E =0			1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 30 V, I _B =0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _c =0			1	μA
DC current gain	h _{FE}	V _{CE} = 2 V, I _c = 1A	60		400	
Collector-emitter saturation voltage	V _{CE (sat)}	I _c = 2A, I _B = 0.2A			0.5	V
Base-emitter saturation voltage	V _{BE (sat)}	I _c = 2A, I _B = 0.2A			1.5	V
Transition frequency	f _T	V _{CE} = 5V, I _c =0.1A f =10MHz		90		MHz



PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SD882	TO-252	2500

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